

Rudra Sankar Dhar

List of Publications by Year in descending order

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43
papers

178
citations

1684188

5
h-index

1199594

12
g-index

50
all docs

50
docs citations

50
times ranked

180
citing authors

#	ARTICLE	IF	CITATIONS
1	Measuring the exciton diffusion length of C ₆₀ in organic planar heterojunction solar cells. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 1967-1971.	1.8	36
2	Direct Nanoscale Imaging of Evolving Electric Field Domains in Quantum Structures. Scientific Reports, 2014, 4, 7183.	3.3	26
3	Development of Tri-Layered Si/SiGe/Si Channel Heterostructure on Insulator MOSFET for Enhanced Drive Current. Physica Status Solidi (B): Basic Research, 2018, 255, 1800034.	1.5	19
4	Direct charge measurements to read back stored data in nonvolatile memory devices using scanning capacitance microscopy. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2013, 31, 061801.	1.2	8
5	Development of double strained Si channel for heterostructure on insulator MOSFET. , 2017, , .		7
6	Performance analysis and development of strain induced quantum well based nano-system device technology. Microsystem Technologies, 2021, 27, 3703-3710.	2.0	7
7	Double strained Si channel heterostructure on insulator MOSFET in sub-100nm regime. , 2017, , .		6
8	Design of DG MOSFET with Tri-Layered Strained Silicon Channel. Journal of Physics: Conference Series, 2020, 1478, 012002.	0.4	5
9	Analysis of mechanical stress and structural deformation on a solar photovoltaic panel through various wind loads. Microsystem Technologies, 2021, 27, 3465-3474.	2.0	5
10	Bio-sensing application of chalcogenide thin film in a graphene-based surface plasmon resonance (SPR) sensor. Sadhana - Academy Proceedings in Engineering Sciences, 2021, 46, 1.	1.3	5
11	Exploration and development of tri-gate quantum well barrier FinFET with strained nanosystem channel for enhanced performance. Computers and Electrical Engineering, 2022, 98, 107687.	4.8	5
12	Two-dimensional profiling of carriers in terahertz quantum cascade lasers using calibrated scanning spreading resistance microscopy and scanning capacitance microscopy. Journal of Microscopy, 2013, 251, 35-44.	1.8	4
13	Electrical scanning probe microscopy of electronic and photonic devices: connecting internal mechanisms with external measures. Nanotechnology Reviews, 2016, 5, .	5.8	4
14	Influence of Design Parameters on Multilayered Nanoplasmonic Structures in Modified Kretschmann-Raether Configurations. Plasmonics, 2020, 15, 1133-1140.	3.4	4
15	Neuro-feedback system for real-time BCI decision prediction. Microsystem Technologies, 2021, 27, 3725-3734.	2.0	4
16	Performance investigations of filtering methods for T1 and T2 weighted infant brain MR images. Microsystem Technologies, 2021, 27, 3711-3723.	2.0	4
17	Exploration of improved leakage based performance analysis for underlap induced strained-Si layer in tri-layered channel DG nanoFETs. Physica Scripta, 2021, 96, 124006.	2.5	4
18	TCAD Modelling of 30nm Strained-Si/SiGe/Si Channel MOSFET. , 2019, , .		3

#	ARTICLE	IF	CITATIONS
19	Estimation and analysis for modelling of stand-alone graphene/AlGaAs/GaAs schottky solar photovoltaic cell module for power conversion efficiency. <i>Microsystem Technologies</i> , 2021, 27, 3693-3701.	2.0	3
20	Development of double strained Si channel for heterostructure on insulator MOSFET. , 2017, , .		2
21	Cell thickness optimization of dual junction InGaP/GaAs solar cell against temperature variation. , 2019, , .		2
22	Strain Engineering Analysis for Nanoscaled Tri-layered Heterostructure-on-Insulator. <i>International Journal of Nanoscience</i> , 2019, , .	0.7	2
23	Modelling and Simulation of 10nm Strained Channel DG- Nano-FET. , 2020, , .		2
24	Physics & Modeling of Ambipolar Snapback Behavior in Gate Grounded NMOS. <i>Silicon</i> , 2022, 14, 3221-3231.	3.3	2
25	Fabrication and characterization of copper based semiconducting materials for optoelectronic applications. <i>Microsystem Technologies</i> , 2021, 27, 3475-3482.	2.0	2
26	Efficient Optimization Technique for Analysing the Performance of Bifacial Solar Cells Using Fuzzy Logic. <i>Lecture Notes in Networks and Systems</i> , 2022, , 263-272.	0.7	2
27	Development and Characterization of Nano Material Membrane Device for Enhanced Transmittance. , 2021, , .		1
28	Comparative performance analysis based short channel effects for TG Nano FinFETs. <i>Journal of Physics: Conference Series</i> , 2021, 1921, 012014.	0.4	1
29	TCAD Modeling and Analysis of sub-30nm Strained Channel MOSFET. <i>Algorithms for Intelligent Systems</i> , 2020, , 1383-1388.	0.6	1
30	Determination of Enriched Quantum Efficiency with InGaN/GaN Multiple Quantum Well Solar Cells. <i>Micro and Nanosystems</i> , 2021, 13, 418-425.	0.6	1
31	Micro-features of ambipolar snapback behaviour under high current injection to design capacitorless memory device. <i>Physica Scripta</i> , 2021, 96, 124069.	2.5	1
32	Nanosopic voltage distribution of operating cascade laser devices in cryogenic temperature. <i>Journal of Microscopy</i> , 2016, 262, 226-231.	1.8	0
33	Investigation of 30nm Tri-layered Strained Silicon HOI MOSFET using TCAD. , 2018, , .		0
34	Two Strained-Si Layers in Channel Region of HOI MOSFET. , 2018, , .		0
35	Double Strained Channel MOSFET: Deep Into Sub-Microns. , 2018, , .		0
36	Design of Double Gate Nano-FET. , 2019, , .		0

#	ARTICLE	IF	CITATIONS
37	Significance of Different Buffer Layers in an SPR Multichannel Sensor. , 2020, , .		0
38	TCAD Based Optimization of SJ Infrared Solar Cell for an Efficient Thermo-Photovoltaic Application. , 2020, , .		0
39	Utility of a Reverse Double-drift Structure for Fabricating GaN IMPATT Diode Operating in the Terahertz Regime. Journal of Nano- and Electronic Physics, 2021, 13, 03014-1-03014-4.	0.5	0
40	Performance Estimation and Analysis of 3D Trigate HOI FinFET Using Strained Channel for Reduced Area. Lecture Notes in Electrical Engineering, 2021, , 289-299.	0.4	0
41	Analysis of Capacitanceâ€“Voltage Characteristics for Ultrathin Si/SiGe/Si Hetero-Layered MOS Structure. Advances in Intelligent Systems and Computing, 2020, , 83-89.	0.6	0
42	Bipolar effects in snapback mechanism in advanced n-FET transistors under high current stress conditions. Journal of Physics Communications, 2020, 4, 065009.	1.2	0
43	Fabrication and analysis of emerging electrochromic nanomaterial membrane device for smart applications. Journal of Materials Science: Materials in Electronics, 0, , 1.	2.2	0